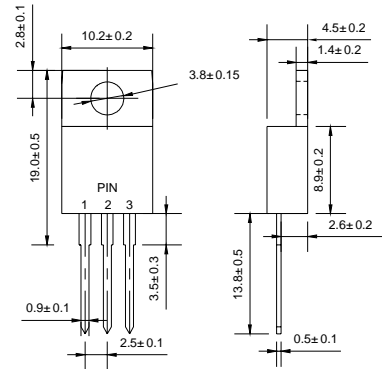



TO-220AB
FEATURES

- ◇ Metal-Semiconductor Junction With Guard Ring.
- ◇ Epitaxial Construction.
- ◇ Low Forward Voltage Drop, Low Switching Losses.
- ◇ High Surge Capacity.
- ◇ For Use in Low Voltage, High Frequency Inverters Free
- ◇ Wheeling, and Polarity Protection Applications.



Lead-free



Dimensions in millimeters

MAXIMUM RATING operating temperature range applies unless otherwise specified

Symbol	Parameter	MBR20150CT	MBR20200CT	Unit
V_{RRM}	Recurrent Peak Reverse Voltage	150	200	V
V_{RMS}	RMS Reverse Voltage	105	140	V
V_{DC}	DC Blocking Voltage	150	200	V
$I_{(AV)}$	Average Forward Total Device Rectified Current @ $T_A=100^{\circ}C$	20		A
I_{FSM}	Peak Forward Surge Current 8.3ms Single Half Sine-wave Superimosed on Rated Load	150		A
$R_{\theta JC}$	Typical Thermal Resistance Junction to Case (Note 1)	1.5		$^{\circ}C/W$
$T_j T_{stg}$	Operating Junction and Storage Temperature Range	-55 to +150		$^{\circ}C$

ELECTRICAL CHARACTERISTICS @ $T_a=25^{\circ}C$ unless otherwise specified

Parameter	Symbol	Test conditions	MBR20150CT	MBR20200CT	UNIT
			MAX		
Reverse Current	I_R	$V_R=V_{RRM}, T_A=25^{\circ}C$ $V_R=V_{RRM}, T_A=125^{\circ}C$	0.1 50		mA
Forward Voltage	V_F	$I_F=10A$	0.90	0.95	V



MBR20150CT, MBR20200CT

Sckottky Barrier Rectifier

TYPICAL CHARACTERISTICS @ $T_a=25^{\circ}\text{C}$ unless otherwise specified

FIG.1 TYPICAL FORWARD CHARACTERISTICS

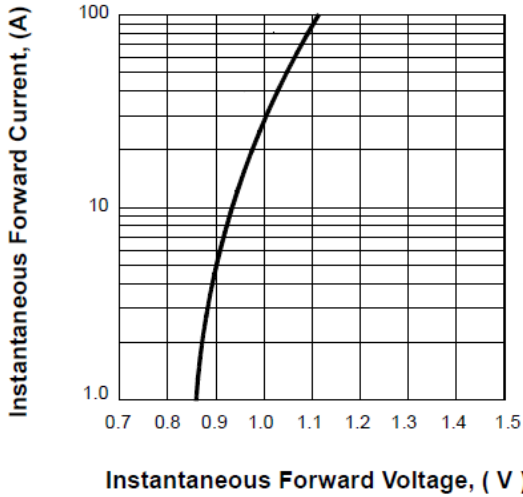


FIG.2 FORWARD DERATING CURVE

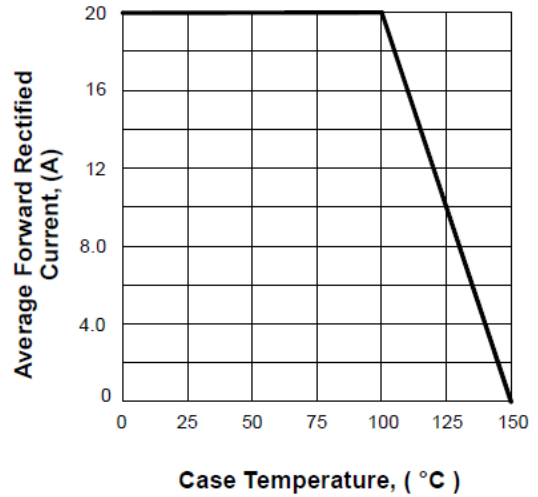


FIG.3 TYPICAL REVERSE CHARACTERISTICS

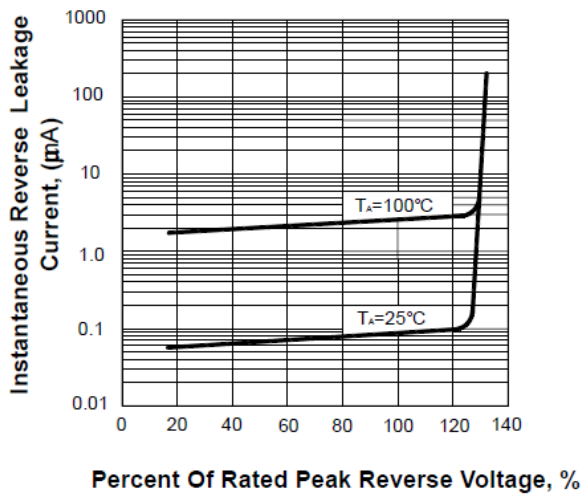


FIG.4 PEAK FORWARD SURGE CURRENT

